

MMDT5551

160V DUAL NPN HIGH-VOLTAGE TRANSISTOR IN SOT363

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type MMDT5401
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface-Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
 A listing can be found at

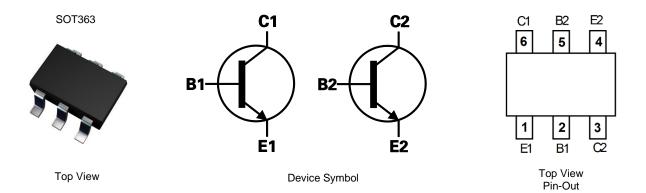
https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound,
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (Approximate)



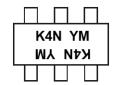
Ordering Information (Note 4)

Orderable Part Number	Paakaga	Marking	ing Reel Size (inches) Tape Width (mm)		Pac	king
Orderable Part Number	Package	Marking	Reel Size (inches)	rape width (mm)	Qty.	Carrier
MMDT5551-7-F	SOT363	K4N	7	8	3,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K4N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: M = 2025) M = Month (ex: 5 = May)

Date Code Key

Year	2012	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	Z	-	М	Ν	Р	R	S	Т	U	V	W	Χ
	1	ı										
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	VCEO	160	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Dawer Dissipation	(Note 5)	Б	200	mW	
Power Dissipation	(Notes 6 & 7)	P_D	320		
Thermal Desistance Investigate Archivet	(Note 5)	5	625		
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	Reja	390	°C/W	
Thermal Resistance, Junction to Case (Note 8)		R ₀ JC	140		
Operating and Storage Temperature Range	<u>.</u>	T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady state.

 6. Same as Note 5, except the device is mounted 25mm × 25mm 2oz copper.
- 7. Maximum combined dissipation.
- 8. Thermal resistance from junction to the top of package.

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С
Electrostatic Discharge – Charged Device Model	ESD CDM	1,000	V	IV

Note:

Thermal Characteristics and Derating Information

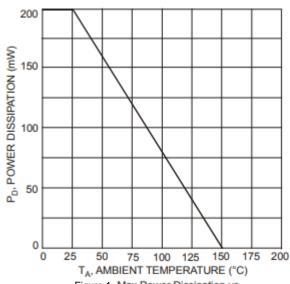


Figure 1. Max Power Dissipation vs. Ambient Temperature

^{9.} Refer to JEDEC specification JESD22-A114, JESD22-A115 and JES-022-C101.



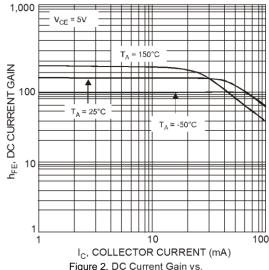
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	ВУсво	180	_		V	$I_C = 100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 10)	BVceo	160	_		V	$I_C = 1 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BVEBO	6	_	_	٧	I _E = 10μA, I _C = 0	
Collector-Base Cutoff Current	lone	_	_	50	nA	V _{CB} = 120V, I _E = 0	
Collector-Base Cuton Current	Ісво	_	_	50	μΑ	V _{CB} = 120V, I _E = 0, T _A = +100°C	
Base-Emitter Cutoff Current	I _{EBO}	_		50	nA	V _{EB} = 4V, I _C = 0	
ON CHARACTERISTICS (Note 10)							
		80		_		Ic = 1mA, VcE = 5.0V	
DC Current Gain	hFE	80	_	250	_	Ic = 10mA, VcE = 5.0V	
		30			<u></u>	I _C = 50mA, V _{CE} = 5.0V	
Collector-Emitter Saturation Voltage	V			0.15	V	Ic = 10mA, I _B = 1.0mA	
Collector-Emitter Saturation voltage	V _{CE(sat)}			0.20	V	Ic = 50mA, I _B = 5.0mA	
Page Emitter Saturation Voltage	1/			1.0	V	Ic = 10mA, I _B = 1.0mA	
Base-Emitter Saturation Voltage	V _{BE(sat)}	BE(sat) —				Ic = 50mA, I _B = 5.0mA	
SMALL-SIGNAL CHARACTERISTICS							
Output Capacitance	Cobo	_	_	6.0	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0	
Small-Signal Current Gain	h _{fe}	50	_	250	-	Ic = 1mA, VcE = 10V, f = 1.0MHz	
Current Gain-Bandwidth Product	f⊤	100	_	300	MHz	I _C = 10mA, V _{CE} = 10V, f = 100MHz	
Noise Figure	NF	_	_	8.0	dB	$V_{CE} = 5.0V$, $I_C = 200\mu A$, $R_S = 1k\Omega$, $f = 1.0kHz$	

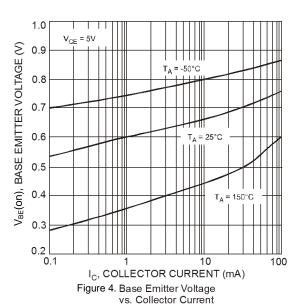
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







0.15 0.14 V_{CE}(sat), COLLECTOR TO EMITTER SATURATION VOLTAGE (V) 0.13 0.12 0.11 0.10 0.09 0.08 0.07 0.06 0.05 T_A = -50°C 0.04 10 100 1,000 $I_{\rm C}$, COLLECTOR CURRENT (mA)

Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

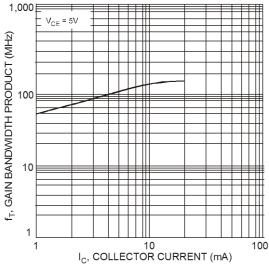


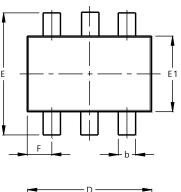
Figure 5. Gain Bandwidth Product vs. Collector Current

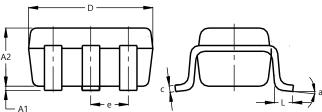


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



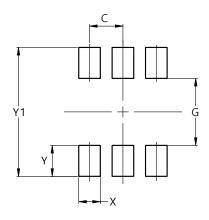


	SOT363						
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	.650 E	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions	in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value
Dimensions	(in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

Note: For high-voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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